勝 特 力 材 料 886-3-5753170 胜特力电子(上海) 86-21-54151736 胜特力电子(深圳) 86-755-83298787 Http://www.100y.com.tw

#### **Features**

- . Low-Voltage and Standard-Voltage Operation
  - $-2.7 (V_{CC} = 2.7V \text{ to } 5.5V)$
  - $1.8 (V_{CC} = 1.8V \text{ to } 5.5V)$
- 3-Wire Serial Interface
- 2 MHz Clock Rate (5V) Compatibility
- Self-Timed Write Cycle (10 ms max)
- High Reliability
  - Endurance: 1 Million Write Cycles
  - Data Retention: 100 Years
- Automotive Grade, Extended Temperature, and Lead-Free/Halogen-Free Devices Available
- 8-lead PDIP, 8-lead JEDEC SOIC, and 8-lead TSSOP Packages

# **Description**

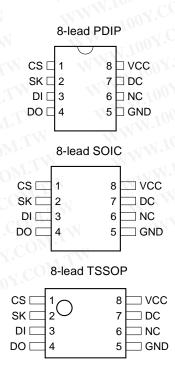
The AT93C46A provides 1024 bits of serial electrically erasable programmable read only memory (EEPROM) organized as 64 words of 16 bits each. The device is optimized for use in many industrial and commercial applications where low power and low voltage operation are essential. The AT93C46A is available in space saving 8-lead PDIP, 8-lead JEDEC SOIC, and 8-lead TSSOP packages.

The AT93C46A is enabled through the Chip Select pin (CS), and accessed via a 3-wire serial interface consisting of Data Input (DI), Data Output (DO), and Shift Clock (SK). Upon receiving a READ instruction at DI, the address is decoded and the data is clocked out serially on the data output pin DO. The WRITE cycle is completely self-timed and no separate ERASE cycle is required before WRITE. The WRITE cycle is only enabled when the part is in the ERASE/WRITE ENABLE state. When CS is brought "high" following the initiation of a WRITE cycle, the DO pin outputs the READY/BUSY status of the part.

The AT93C46A is available in 2.7V to 5.5V and 1.8V to 5.5V versions.

# **Pin Configurations**

Pin Name	Function		
CS	Chip Select		
SK	Serial Data Clock		
DI	Serial Data Input		
DO	Serial Data Output		
GND	Ground		
VCC	Power Supply		
NC	No Connect		
DC	Don't Connect		





# 3-Wire Serial EEPROM 1K (64 x 16)

# **AT93C46A**

Rev. 0539G-SEEPR-12/03





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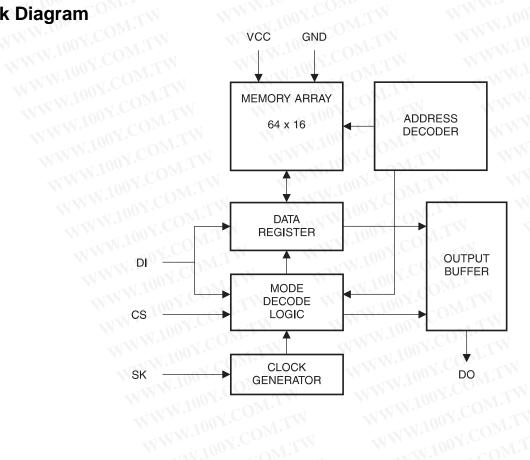
# WWW.100Y.COM.TW **Absolute Maximum Ratings\***

Operating Temperature	55°C to +125°C
Storage Temperature	65°C to +150°C
Voltage on Any Pin with Respect to Ground	1.0V to +7.0V
Maximum Operating Voltage	6.25V
DC Output Current	5.0 mA

\*NOTICE:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## **Block Diagram**



Http://www. 100y. com. tw

# **Pin Capacitance**

Applicable over recommended operating range from  $T_A = 25$ °C, f = 1.0 MHz,  $V_{CC} = +5.0$ V (unless otherwise noted).

Symbol	Test Conditions	Max	Units	Conditions
C <sub>OUT</sub>	Output Capacitance (DO)	5	CO pF	$V_{OUT} = 0V$
C <sub>IN</sub>	Input Capacitance (CS, SK, DI)	5	CpF	$V_{IN} = 0V$

Note: This parameter is characterized and is not 100% tested.

## **DC Characteristics**

Applicable over recommended operating range from:  $T_{AI} = -40^{\circ}C$  to  $+85^{\circ}C$ ,  $V_{CC} = +1.8V$  to +5.5V, (unless otherwise noted).

Symbol	Parameter	Test Condition		Min	Тур	Max	Units
V <sub>CC1</sub>	Supply Voltage	WWW. 100X.COM.TY		1.8	WW.10	5.5	V
V <sub>CC2</sub>	Supply Voltage	IN WW	1100Y.COM.	2.7	WW TANA	5.5	TV
V <sub>CC3</sub>	Supply Voltage	TW WY	1100 Y. CO.	4.5	MM	5.5	V
. 1	WW. CON	WW FOW W	READ at 1.0 MHz	ITW	0.5	2.0	mA
I <sub>CC</sub>	Supply Current	$V_{CC} = 5.0V$	WRITE at 1.0 MHz	WIN	0.5	2.0	mA
I <sub>SB1</sub>	Standby Current	V <sub>CC</sub> = 1.8V		WILL	14.0	20.0	μA
I <sub>SB2</sub>	Standby Current	V <sub>CC</sub> = 2.7V	CS = 0V	OM	14.0	20.0	μA
I <sub>SB3</sub>	Standby Current	V <sub>CC</sub> = 5.0V	CS = 0V	ON	35.0	50.0	μА
I <sub>IL</sub>	Input Leakage	V <sub>IN</sub> = 0V to V <sub>CC</sub>		COM	0.1	1.0	μA
I <sub>OL</sub>	Output Leakage	$V_{IN} = 0V \text{ to } V_{CC}$	MMM.Too	C.COM.	0.1	1.0	μA
V <sub>IL1</sub> <sup>(1)</sup> V <sub>IH1</sub> <sup>(1)</sup>	Input Low Voltage Input High Voltage	4.5V ≤ V <sub>CC</sub> ≤ 5.5V	COM'3		TW .	0.8 V <sub>CC</sub> + 1	001 V
V <sub>IL2</sub> <sup>(1)</sup> V <sub>IH2</sub> <sup>(1)</sup>	Input Low Voltage Input High Voltage	1.8V ≤ V <sub>CC</sub> ≤ 2.7V		-0.6 V <sub>CC</sub> x 0.7	V.I.M	V <sub>CC</sub> x 0.3 V <sub>CC</sub> + 1	100 V.C
V <sub>OL1</sub>	Output Low Voltage	450 20 25 50	I <sub>OL</sub> = 2.1 mA	1001.CO	M.TW	0.4	VIVY
V <sub>OH1</sub>	Output High Voltage	$4.5V \le V_{CC} \le 5.5V$	I <sub>OH</sub> = -0.4 mA	2.4	WIIM	MM	VO
V <sub>OL2</sub>	Output Low Voltage	4.01/21/2	I <sub>OL</sub> = 0.15 mA	100Y.C	WILM	0.2	V
V <sub>OH2</sub>	Output High Voltage	$1.8V \le V_{CC} \le 2.7V$	Ι <sub>ΟΗ</sub> = -100 μΑ	V <sub>CC</sub> - 0.2	COM	V V	V

Note: 1.  $V_{IL}$  min and  $V_{IH}$  max are reference only and are not tested.





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#### **AC Characteristics**

Applicable over recommended operating range from  $T_A = -40$ °C to + 85°C,  $V_{CC} = +2.5$ V to + 5.5V, CL = 1 TTL Gate and 100 pF (unless otherwise noted).

Symbol	Parameter	Test Condition	WILL	Min	Тур	Max	Units
f <sub>sk</sub>	SK Clock Frequency	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	COM.	0 0 0	100X.C	2 1 0.25	MHz
t <sub>skh</sub>	SK High Time	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	COM	250 250 1000	W.100Y	COM.TY	ns
t <sub>SKL</sub>	SK Low Time	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	No. COM.	250 250 1000	MW.100	ox.com	TW ns
t <sub>cs</sub>	Minimum CS Low Time	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	1.100 COM.	250 250 1000	MMM;	100X·CO	ns
t <sub>CSS</sub>	CS Setup Time	Relative to SK	$ 4.5V \le V_{CC} \le 5.5V \\ 2.7V \le V_{CC} \le 5.5V \\ 1.8V \le V_{CC} \le 5.5V $	50 50 200	MM	A 100X.C	ns
t <sub>DIS</sub>	DI Setup Time	Relative to SK	$ 4.5V \le V_{CC} \le 5.5V $ $ 2.7V \le V_{CC} \le 5.5V $ $ 1.8V \le V_{CC} \le 5.5V $	100 100 400	W	VW.100Y	CO ns
t <sub>CSH</sub>	CS Hold Time	Relative to SK	WWW. 100Y.C	0 1	V	100	ns
t <sub>DIH</sub>	DI Hold Time	Relative to SK	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	100 100 400		MMM.10	oy. es
t <sub>PD1</sub>	Output Delay to '1'	AC Test	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	Y.COM	TW	250 250 1000	ns O
t <sub>PD0</sub>	Output Delay to '0'	AC Test	$4.5V \le V_{CC} \le 5.5V$ $2.7V \le V_{CC} \le 5.5V$ $1.8V \le V_{CC} \le 5.5V$	100X·CON	A.TW	250 250 1000	ns C
t <sub>SV</sub>	CS to Status Valid	AC Test	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	100Y.C	OM.TW OM.TW	250 250 1000	ns
t <sub>DF</sub>	CS to DO in High Impedance	AC Test CS = V <sub>IL</sub>	$\begin{array}{c} 4.5 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 2.7 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \\ 1.8 \text{V} \leq \text{V}_{\text{CC}} \leq 5.5 \text{V} \end{array}$	W.100Y	COM.T	100 100 400	ns ns
4	Write Cycle Time	M. TOON CON	W WI	7 100	A.Co.	10	ms
T <sub>WP</sub>	Write Cycle Time	AM.TOOX.CO	4.5V ≤ V <sub>CC</sub> ≤ 5.5V	MAN	3	TW	ms
	5.0V, 25°C, Page Mode	zed and is not 100	) Name of the last	1M	ON.COD		Write Cycle

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#### Instruction Set for the AT93C46A

N.To.		V V	Address	CONTW WWW. 100Y.COM.TW			
Instruction	SB	Op Code	x 16	Comments			
READ		10	A <sub>5</sub> - A <sub>0</sub>	Reads data stored in memory, at specified address.			
EWEN	$CO_{M}$	00	11XXXX	Write enable must precede all programming modes.			
ERASE	101	11	A <sub>5</sub> - A <sub>0</sub>	Erase memory location A <sub>n</sub> - A <sub>0</sub> .			
WRITE	10	01	A <sub>5</sub> - A <sub>0</sub>	Writes memory location A <sub>n</sub> - A <sub>0</sub> .			
ERAL	1	00	10XXXX	Erases all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V.			
WRAL	001	00	01XXXX	Writes all memory locations. Valid only at $V_{CC} = 4.5V$ to 5.5V.			
EWDS	100	00	00XXXX	Disables all programming instructions.			

# Functional Description

The AT93C46A is accessed via a simple and versatile three-wire serial communication interface. Device operation is controlled by seven instructions issued by the host processor. A valid instruction starts with a rising edge of CS and consists of a Start Bit (logic "1") followed by the appropriate Op Code and the desired memory Address location.

**READ (READ):** The Read (READ) instruction contains the Address code for the memory location to be read. After the instruction and address are decoded, data from the selected memory location is available at the serial output pin DO. Output data changes are synchronized with the rising edges of serial clock SK. It should be noted that a dummy bit (logic "0") precedes the 16-bit data output string.

**ERASE/WRITE (EWEN):** To assure data integrity, the part automatically goes into the Erase/Write Disable (EWDS) state when power is first applied. An Erase/Write Enable (EWEN) instruction must be executed first before any programming instructions can be carried out. Please note that once in the Erase/Write Enable state, programming remains enabled until an Erase/Write Disable (EWDS) instruction is executed or V<sub>CC</sub> power is removed from the part.

**ERASE (ERASE):** The Erase (ERASE) instruction programs all bits in the specified memory location to the logical "1" state. The self-timed erase cycle starts once the ERASE instruction and address are decoded. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns ( $t_{\rm CS}$ ). A logic "1" at pin DO indicates that the selected memory location has been erased, and the part is ready for another instruction.

**WRITE (WRITE):** The Write (WRITE) instruction contains the 16 bits of data to be written into the specified memory location. The self-timed programming cycle,  $t_{WP}$ , starts after the last bit of data is received at serial data input pin DI. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns ( $t_{CS}$ ). A logic "0" at DO indicates that programming is still in progress. A logic "1" indicates that the memory location at the specified address has been written with the data pattern contained in the instruction and the part is ready for further instructions. A READY/BUSY status cannot be obtained if the CS is brought high after the end of the self-timed programming cycle,  $t_{WP}$ 

**ERASE ALL (ERAL):** The Erase All (ERAL) instruction programs every bit in the memory array to the logic "1" state and is primarily used for testing purposes. The DO pin





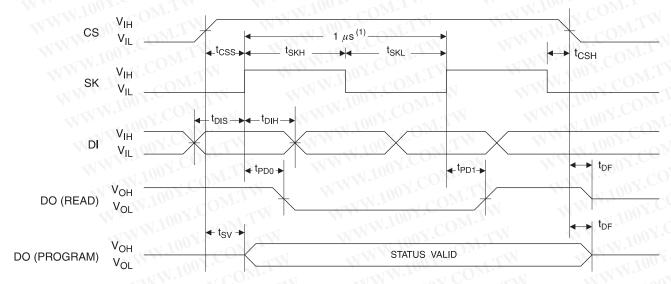
outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns ( $t_{CS}$ ). The ERAL instruction is valid only at  $V_{CC} = 5.0V \pm 10\%$ .

WRITE ALL (WRAL): The Write All (WRAL) instruction programs all memory locations with the data patterns specified in the instruction. The DO pin outputs the READY/BUSY status of the part if CS is brought high after being kept low for a minimum of 250 ns ( $t_{CS}$ ). The WRAL instruction is valid only at  $V_{CC} = 5.0V \pm 10\%$ .

**ERASE/WRITE DISABLE (EWDS):** To protect against accidental data disturb, the Erase/Write Disable (EWDS) instruction disables all programming modes and should be executed after all programming operations. The operation of the READ instruction is independent of both the EWEN and EWDS instructions and can be executed at any time.

# **Timing Diagrams**

#### **Synchronous Data Timing**



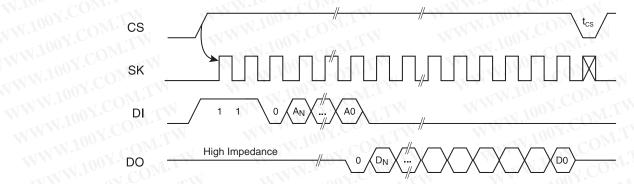
Note: 1. This is the minimum SK period.

# **Organization Key for Timing Diagrams**

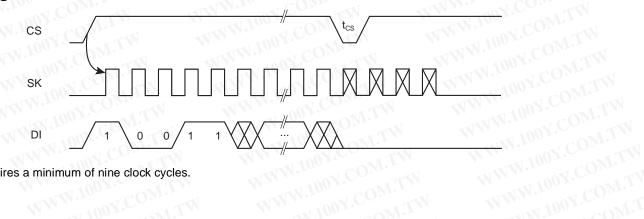
	MM.Inn. COW.	AT93C46A
I/O	M. 100 COW.	x 16
A <sub>N</sub>	M. Ton COM.	A <sub>5</sub> COM
$D_N$	M. TON	D <sub>15</sub>
D <sub>N</sub>	WWW.100X.CO	M.TW

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### **READ Timing**

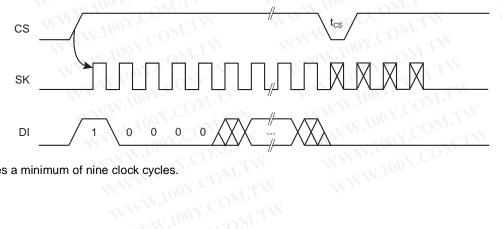


# **EWEN Timing**<sup>(1)</sup>



Note: 1. Requires a minimum of nine clock cycles.

# **EWDS Timing**<sup>(1)</sup>

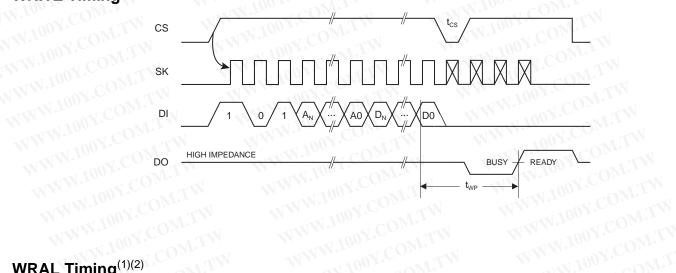


Note: 1. Requires a minimum of nine clock cycles. WWW.100Y.COM.TW

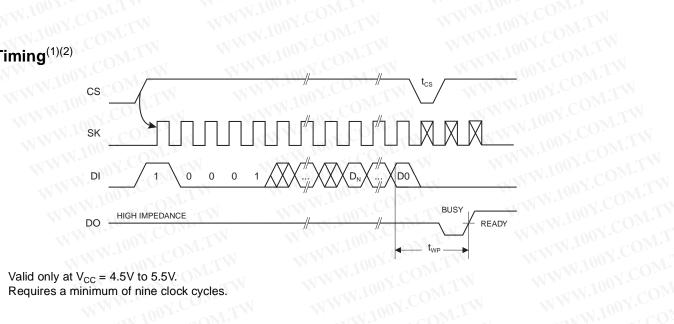


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# WW.100Y.COM.TW **WRITE Timing**



# WRAL Timing<sup>(1)(2)</sup>

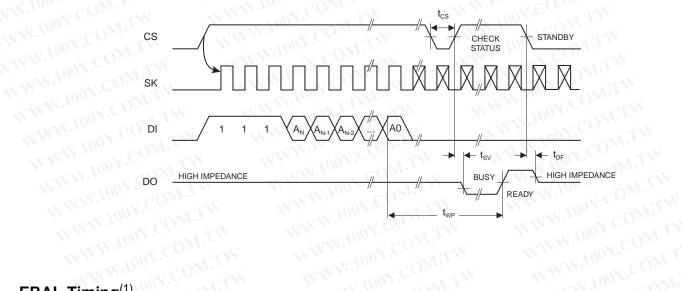


Notes: 1. Valid only at  $V_{CC} = 4.5V$  to 5.5V.

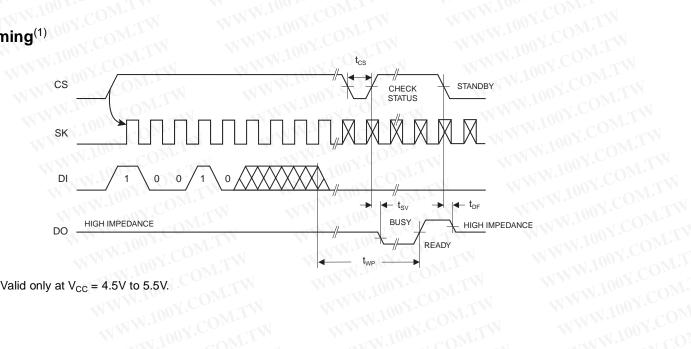
2. Requires a minimum of nine clock cycles. WWW.100Y.COM.TW

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# **ERASE Timing**



# ERAL Timing<sup>(1)</sup>



Note: 1. Valid only at  $V_{CC} = 4.5V$  to 5.5V.



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# WWW.100X.COM.TW WWW.100Y.COM.T **Ordering Information**

Ordering Code	Package	Operation Range	
T93C46A-10PI-2.7	8P3	Industrial	
AT93C46A-10SI-2.7	8S1	(-40°C to 85°C)	
AT93C46A-10TI-2.7	8A2	TI 100Y.COTTY	
AT93C46A-10PI-1.8	8P3	Industrial	
AT93C46A-10SI-1.8	8S1	(-40°C to 85°C)	
AT93C46A-10TI-1.8	8A2	1. 100 J. COM: I.	
AT93C46A-10SU-2.7	8S1	1003: 201:17	
AT93C46A-10SU-1.8	8S1	Lead-Free/Halogen-Free/	
AT93C46A-10TU-2.7	8A2	Industrial Temperature (-40°C to 85°C)	
AT93C46A-10TU-1.8	8A2		

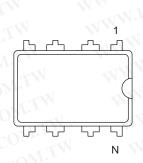
Note: For 2.7V devices used in the 4.5V to 5.5V range, please refer to performance values in the AC and DC characteristics table. WWW.100Y.CO WWW.100Y.C WWW.100Y.C WWW.100Y.COM.TW

	Package Type	
8P3	8-lead, 0.300" Wide, Plastic Dual Inline Package (PDIP)	
8S1	8-lead, 0.150" Wide, Plastic Gull Wing Small Outline (JEDEC SOIC)	
8A2	8-lead, 0.170" Wide, Thin Small Outline Package (TSSOP)	
	Options	
-2.7	Low Voltage (2.7V to 5.5V)	
-1.8	Low Voltage (1.8V to 5.5V)	

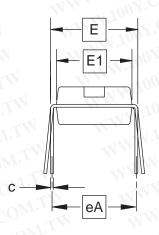
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# **Packaging Information**

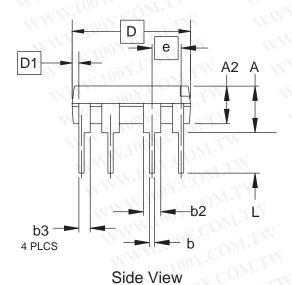
## **8P3 - PDIP**



Top View



**End View** 



#### **COMMON DIMENSIONS**

(Unit of Measure = inches)

SYMBOL	MIN	NOM	MAX	NOTE
Α	ST.	-111	0.210	200
A2	0.115	0.130	0.195	) <u>.</u> .
b	0.014	0.018	0.022	5
b2	0.045	0.060	0.070	6
b3	0.030	0.039	0.045	6
c O	0.008	0.010	0.014	1.100
D	0.355	0.365	0.400	3
D1	0.005		11/4	3 10
EY.C	0.300	0.310	0.325	4
E1	0.240	0.250	0.280	3
е	COM	0.100 BSC	×1	TWW.
eA	CON	0.300 BSC		4
L100	0.115	0.130	0.150	2

Notes:

- 1. This drawing is for general information only; refer to JEDEC Drawing MS-001, Variation BA for additional information.
- 2. Dimensions A and L are measured with the package seated in JEDEC seating plane Gauge GS-3.
- 3. D, D1 and E1 dimensions do not include mold Flash or protrusions. Mold Flash or protrusions shall not exceed 0.010 inch.
- 4. E and eA measured with the leads constrained to be perpendicular to datum.
- 5. Pointed or rounded lead tips are preferred to ease insertion.
- 6. b2 and b3 maximum dimensions do not include Dambar protrusions. Dambar protrusions shall not exceed 0.010 (0.25 mm).

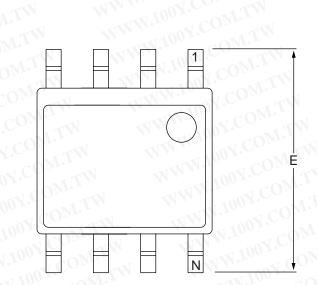
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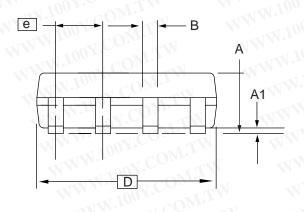


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#### 8S1 - JEDEC SOIC



Top View



Side View

E1.

**End View** 

# **COMMON DIMENSIONS**

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
Α	1.35	- "	1.75	700 x.
A1	0.10	- 1	0.25	1007
<b>b b</b>	0.31	_	0.51	100
cco	0.17	-	0.25	W.r.
D	4.80		5.00	M.In
E1	3.81	_	3.99	TW.1
TEX.	5.79		6.20	NN - TAI
е	COR	1.27 BSC		111111
N.Fo	0.40	- TN	1.27	WWW
Ø	0°	M. F	8°	

Note: These drawings are for general information only. Refer to JEDEC Drawing MS-012, Variation AA for proper dimensions, tolerances, datums, etc.

10/7/03

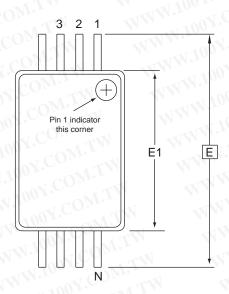
1150 E. Cheyenne Mtn. Blvd. Colorado Springs, CO 80906 TITLE 8S1, 8-lead (0.150" Wide Body), Plastic Gull Wing Small Outline (JEDEC SOIC)

REV. DRAWING NO. 8S1

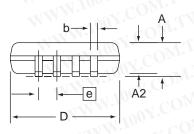
В

Http://www. 100y. com. tw

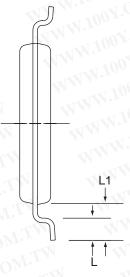
#### 8A2 - TSSOP



Top View



Side View



End View

#### **COMMON DIMENSIONS**

(Unit of Measure = mm)

SYMBOL	MIN	NOM	MAX	NOTE
DCO	2.90	3.00	3.10	2, 5
E CO	Mr.	6.40 BSC	WW	M.r.
E1	4.30	4.40	4.50	3, 5
Α	1.140°	_	1.20	
A2	0.80	1.00	1.05	TAX
b	0.19	W.	0.30	4
е	$^{1.CO_N}$	0.65 BSC		WW
IVI.IUU	0.45	0.60	0.75	TAIN!
L1 10	11.	1.00 REF	-1	1

Notes: 1. This drawing is for general information only. Refer to JEDEC Drawing MO-153, Variation AA, for proper dimensions, tolerances, datums, etc.

- 2. Dimension D does not include mold Flash, protrusions or gate burrs. Mold Flash, protrusions and gate burrs shall not exceed 0.15 mm (0.006 in) per side.
- 3. Dimension E1 does not include inter-lead Flash or protrusions. Inter-lead Flash and protrusions shall not exceed 0.25 mm (0.010 in) per side.
- 4. Dimension b does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the b dimension at maximum material condition. Dambar cannot be located on the lower radius of the foot. Minimum space between protrusion and adjacent lead is 0.07 mm.
- 5. Dimension D and E1 to be determined at Datum Plane H.

5/30/02

